

What is claimed is:

1. A method of manufacturing a semiconductor device, comprising the steps of:

5 forming a conductive layer on a surface of a semiconductor element on which is provided an electrode and electrically connecting the conductive layer to the electrode;

forming a first electrical connecting section on the conductive layer and not above the electrode; and

10 forming a hole in the semiconductor element so that part of a surface of the conductive layer on the side of the semiconductor element is exposed as a second electrical connecting section.